

IGBT Module-Dual

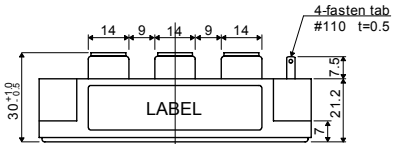
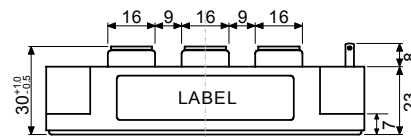
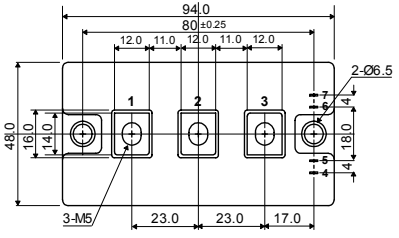
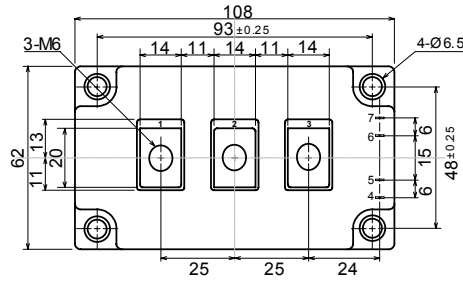
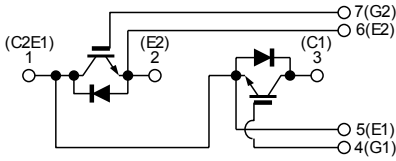
200 A, 1200V

PDMB200BS12

PDMB200BS12C

□ 回路図 : CIRCUIT

□ 外形寸法図 : OUTLINE DRAWING



PDMB200BS12

PDMB200BS12C

Dimension: [mm]

□ 最大定格 : MAXIMUM RATINGS (T_c = 25°C)

Item	Symbol	Rated Value		Unit
コレクタ・エミッタ間電圧 Collector-Emitter Voltage	V _{CEs}	1, 200		V
ゲート・エミッタ間電圧 Gate-Emitter Voltage	V _{GES}	± 20		V
コレクタ電流 Collector Current	DC	200		A
	1ms	400		
コレクタ損失 Collector Power Dissipation	P _C	1, 200		W
接合温度 Junction Temperature Range	T _j	-40 ~ +150		°C
保存温度 Storage Temperature Range	T _{stg}	-40 ~ +125		°C
絶縁耐圧(Terminal to Base AC, 1 minute) Isolation Voltage	V _{ISO}	2, 500		V (RMS)
締め付けトルク Mounting Torque	Module Base to Heatsink Busbar to Main Terminal	PDMB200BS12	3 (30.6)	N · m (kgf · cm)
		PDMB200BS12C	3 (30.6) 2 (20.4)	

□ 電気的特性 : ELECTRICAL CHARACTERISTICS (T_c = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emitter Cut-Off Current	I _{CEs}	V _{CE} = 1200V, V _{GE} = 0V	-	-	2.0	mA
ゲート漏れ電流 Gate-Emitter Leakage Current	I _{GES}	V _{GE} = ±20V, V _{CE} = 0V	-	-	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 200A, V _{GE} = 15V	-	2.3	2.7	V
ゲートしきい値電圧 Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 200mA	4.0	-	8.0	V
入力容量 Input Capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	12,600	-	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	V _{CC} = 600V R _L = 3.0Ω R _G = 7.5Ω V _{GE} = ±15V	-	0.25	0.45	μs
	ターンオン時間 Turn-on Time		-	0.40	0.70	
	下降時間 Fall Time		-	0.25	0.35	
	ターンオフ時間 Turn-off Time		-	0.80	1.10	

□ フリーホイールダイオードの特性 : FREE WHEELING DIODE RATINGS & CHARACTERISTICS (T_c = 25°C)

Item	Symbol	Rated Value		Unit
順電流 Forward Current	DC	200		A
	1ms	400		

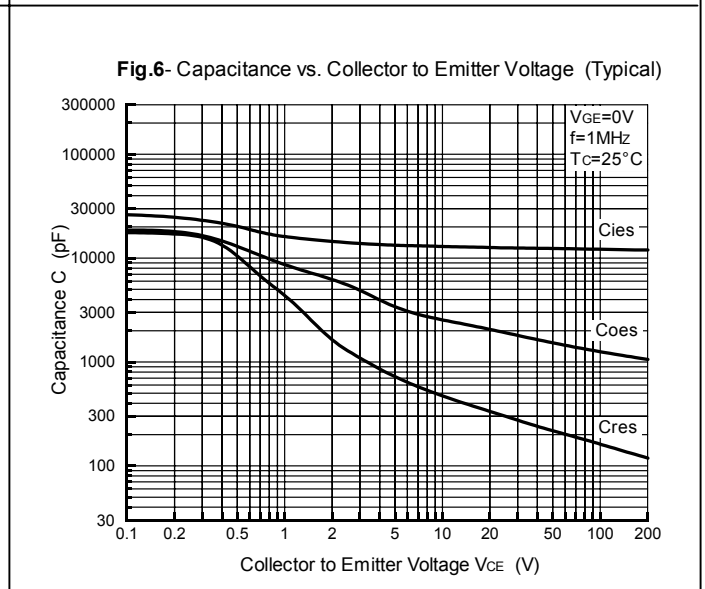
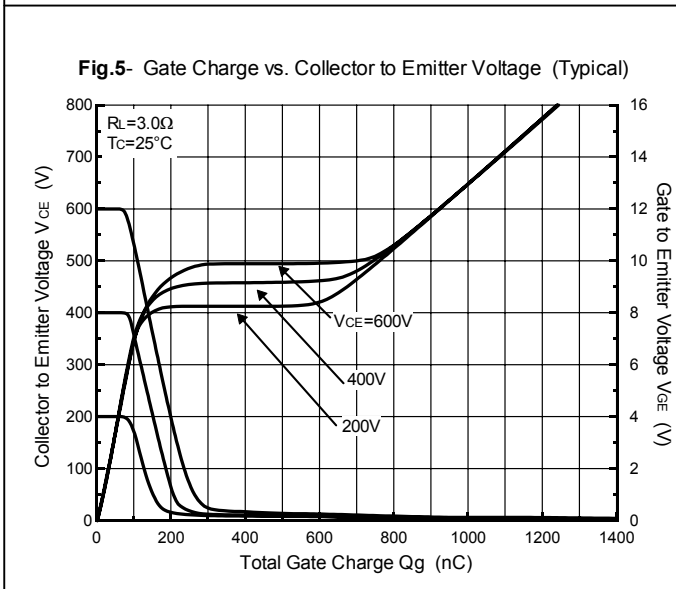
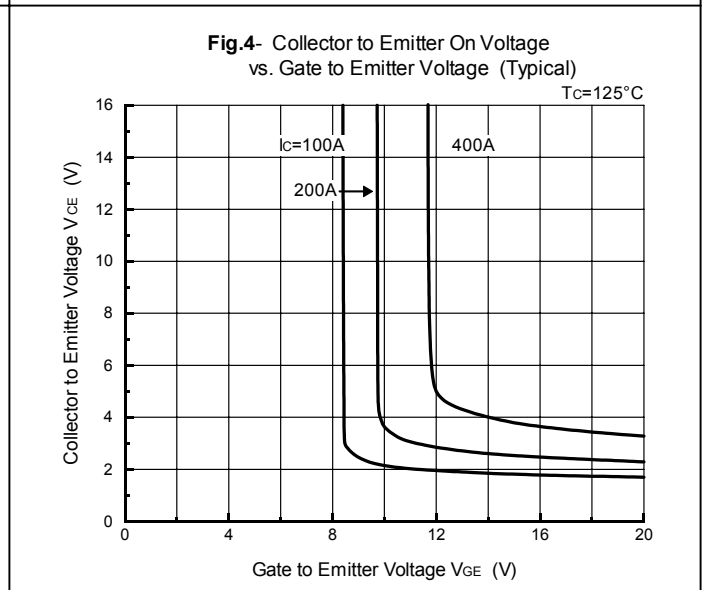
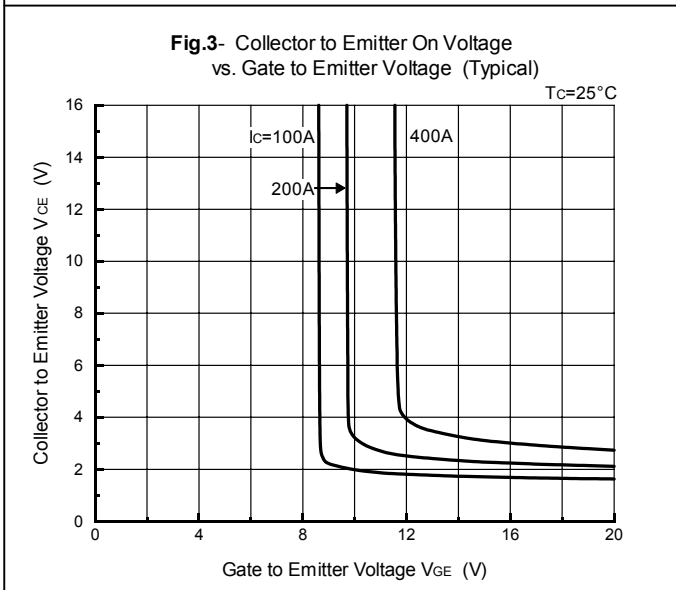
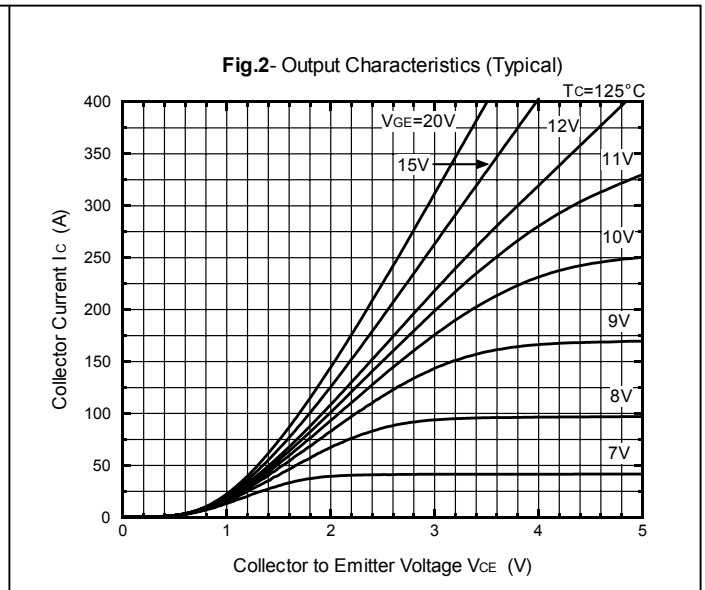
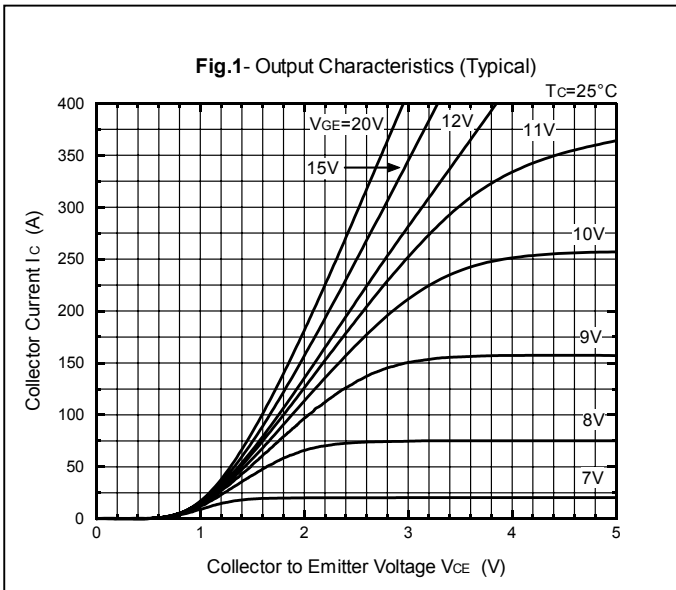
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	V _F	I _F = 200A, V _{GE} = 0V	-	2.2	2.6	V
逆回復時間 Reverse Recovery Time	t _{rr}	I _F = 200A, V _{GE} = -10V di/dt = 400A/μs	-	0.2	0.3	μs

□ 熱的特性 : THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	Junction to Case (T _c 測定点チップ直下)	-	-	0.104	°C/W
	Diode		-	-	0.214	

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Fig.7- Collector Current vs. Switching Time (Typical)

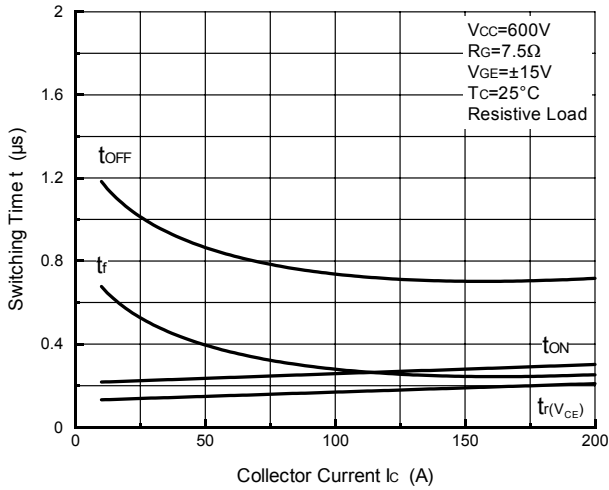


Fig.8- Series Gate Impedance vs. Switching Time (Typical)

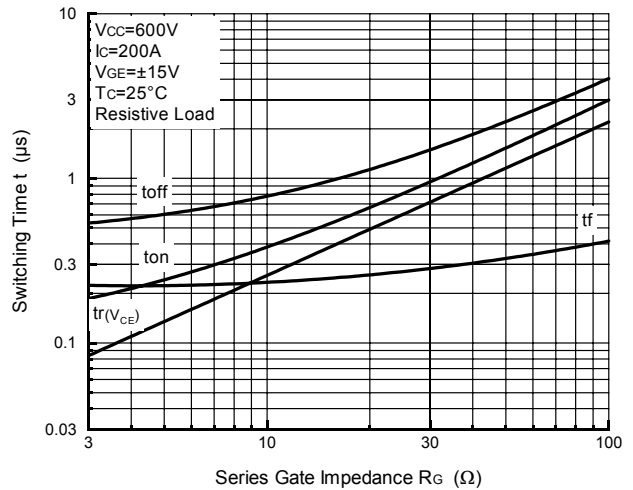


Fig.9- Collector Current vs. Switching Time

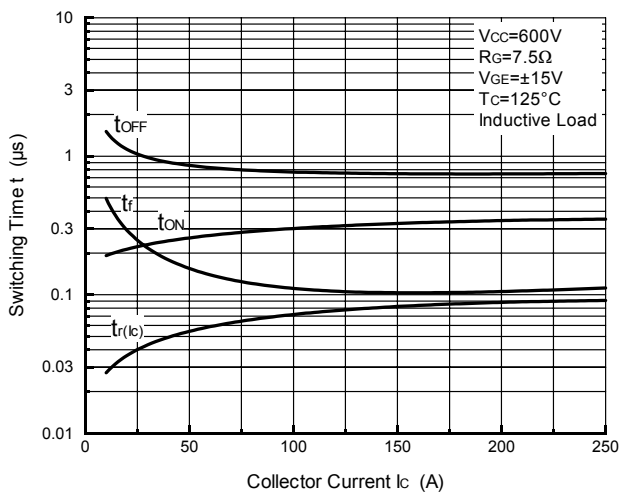


Fig.10- Series Gate Impedance vs. Switching Time

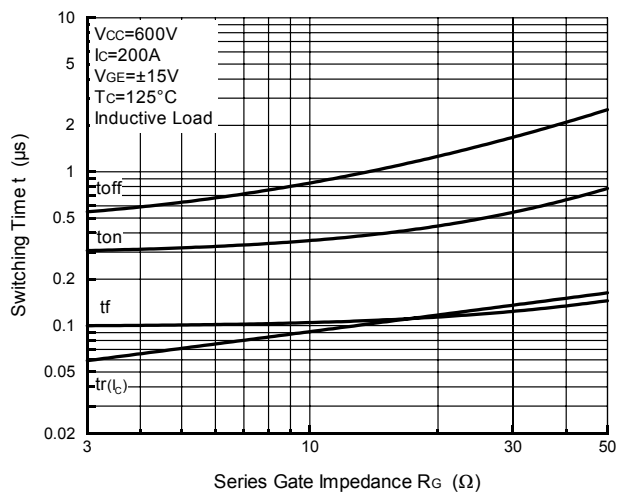


Fig.11- Collector Current vs. Switching Loss

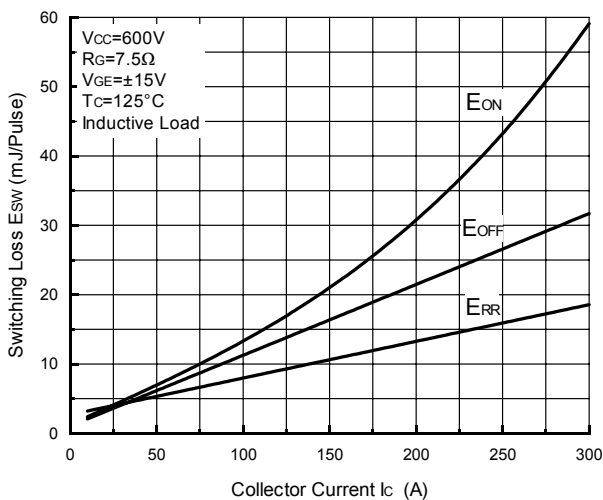
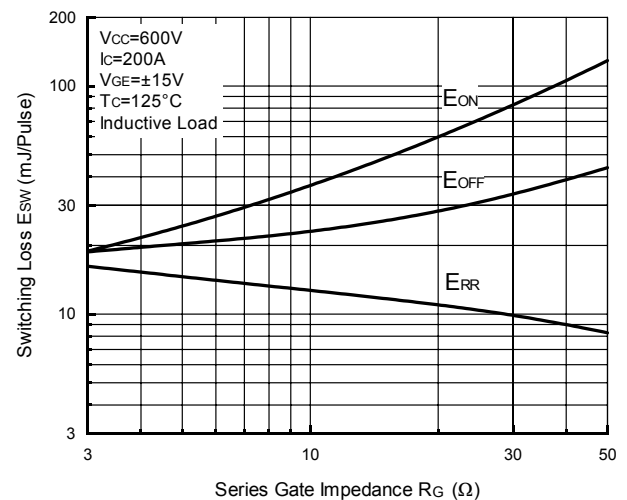


Fig.12- Series Gate Impedance vs. Switching Loss



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